

PHN203

Dual N-channel TrenchMOS logic level FET

Rev. 05 — 27 April 2010

Product data sheet

1. Product profile

1.1 General description

Dual logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

1.2 Features and benefits

- Suitable for high frequency applications due to fast switching characteristics
- Suitable for logic level gate drive sources

1.3 Applications

■ DC-to-DC converters

■ Lithium-ion battery applications

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	$T_j \ge 25 \text{ °C}; T_j \le 150 \text{ °C}$		-	-	30	V
I _D	drain current	T _{amb} = 25 °C; pulsed; see <u>Figure 1</u> ; see <u>Figure 3</u>	[1]	-	-	6.3	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C; pulsed; see <u>Figure 2</u>	[1]	-	-	2	W
Static chara	acteristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 7 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see <u>Figure 9</u> ; see <u>Figure 10</u>		-	24	30	mΩ
Dynamic ch	naracteristics						
Q_{GD}	gate-drain charge	V_{GS} = 10 V; I_D = 7 A; V_{DS} = 15 V; T_j = 25 °C; see <u>Figure 11</u>		-	3	-	nC

^[1] Single device conducting.



Dual N-channel TrenchMOS logic level FET

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source1		D. D. D. D. D.
2	G1	gate1	8 <u>A A A A</u>	D1 D1 D2 D2
3	S2	source2		
4	G2	gate2		
5	D2	drain2	1	
6	D2	drain2	SOT96-1 (SO8)	S1 G1 S2 G2
7	D1	drain1		mbk725
8	D1	drain1		

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PHN203	SO8	plastic small outline package; 8 leads; body width 3.9 mm	SOT96-1

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 150 °C		-	-	30	V
V_{DGR}	drain-gate voltage	$T_j \le 150 \text{ °C}; T_j \ge 25 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$		-	-	30	V
V_{GS}	gate-source voltage			-20	-	20	V
I_D	drain current	T _{amb} = 70 °C; pulsed; see Figure 1	[1]	-	-	5	Α
		T _{amb} = 25 °C; pulsed; see <u>Figure 1</u> ; see <u>Figure 3</u>	[1]	-	-	6.3	Α
I _{DM}	peak drain current	t $t_p \le 10 \mu s$; pulsed; $T_{amb} = 25 \text{ °C}$; see Figure 3		-	-	18	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C; pulsed; see Figure 2	<u>[1]</u>	-	-	2	W
T _{stg}	storage temperature			-55	-	150	°C
Tj	junction temperature			-55	-	150	°C
Source-drain	n diode						
Is	source current	T _{amb} = 25 °C; pulsed	<u>[1]</u>	-	-	2	Α
I _{SM}	peak source current	$t_p \le 10 \ \mu s$; pulsed; $T_{amb} = 25 \ ^{\circ}C$	<u>[1]</u>	-	-	4.1	Α
Avalanche ru	uggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 8.7 A; $V_{sup} \le$ 30 V; unclamped; t_p = 0.2 ms; R_{GS} = 50 Ω		-	-	37.8	mJ

^[1] Single device conducting.

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PHN203

Dual N-channel TrenchMOS logic level FET

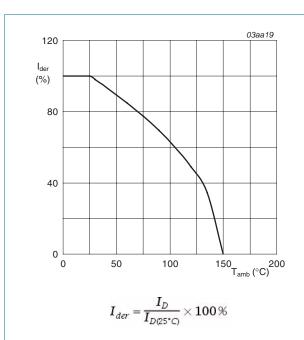


Fig 1. Normalized continuous drain current as a function of ambient temperature

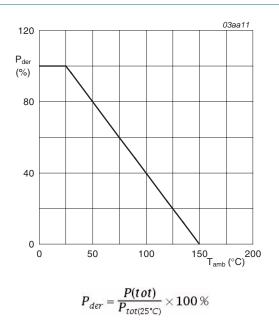
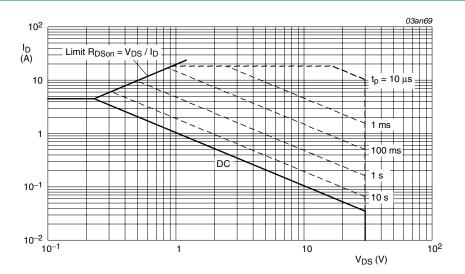


Fig 2. Normalized total power dissipation as a function of ambient temperature



 $T_{amb} = 25$ °C; I_{DM} is single pulse; $V_{GS} = 10V$

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

Dual N-channel TrenchMOS logic level FET

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j\text{-sp})}$	thermal resistance from junction to solder point		-	-	-	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	mounted on a printed-circuit board; minimum footprint; see Figure 4	-	-	62.5	K/W

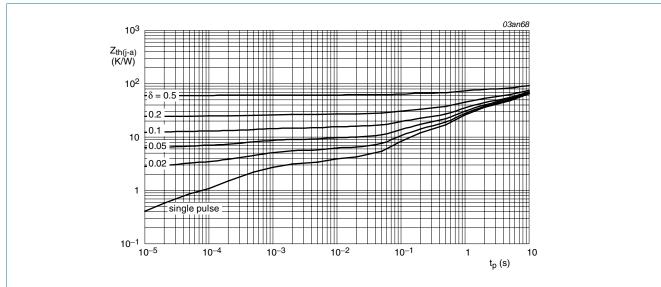


Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration

Dual N-channel TrenchMOS logic level FET

6. Characteristics

Table 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
$V_{(BR)DSS}$	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	27	-	-	V
	breakdown voltage	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$	30	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = -55 \text{ °C}$; see <u>Figure 8</u>	-	-	2.2	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 150$ °C; see <u>Figure 8</u>	0.6	-	-	V
		$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = 25 \text{ °C}$; see Figure 8	1	1.5	2	V
I _{DSS}	drain leakage current	$V_{DS} = 24 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μΑ
		$V_{DS} = 24 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 ^{\circ}\text{C}$	-	-	10	μΑ
I _{GSS}	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nA
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nA
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 7 A; T_j = 25 °C; see <u>Figure 9</u> ; see <u>Figure 10</u>	-	24	30	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 3.5 \text{ A}; T_j = 25 \text{ °C};$ see <u>Figure 9</u> ; see <u>Figure 10</u>	-	30	55	mΩ
		V_{GS} = 10 V; I_D = 7 A; T_j = 150 °C; see <u>Figure 9</u> ; see <u>Figure 10</u>	-	40.8	51	mΩ
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 7 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 10 \text{ V};$	-	14.6	-	nC
Q _{GS}	gate-source charge	T _j = 25 °C; see <u>Figure 11</u>	-	2	-	nC
Q_{GD}	gate-drain charge		-	3	-	nC
C _{iss}	input capacitance	$V_{DS} = 20 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	560	-	рF
Coss	output capacitance	T _j = 25 °C; see <u>Figure 12</u>	-	125	-	pF
C_{rss}	reverse transfer capacitance	V_{DS} 20 V; V_{GS} = 0 V; f = 1 MHz; T_j = 25 °C; see Figure 12	-	85	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 25 \text{ V}; R_L = 25 \Omega; V_{GS} = 10 \text{ V};$	-	5	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	6	-	ns
t _{d(off)}	turn-off delay time		-	21	-	ns
t _f	fall time		-	11	-	ns
Source-di	rain diode					
V_{SD}	source-drain voltage	$I_S = 1.25 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_j = 25 \text{ °C}$; see <u>Figure 13</u>	-	0.75	1	V
t _{rr}	reverse recovery time	$I_S = 2 \text{ A}; dI_S/dt = -100 \text{ A}/\mu\text{s}; V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; T_i = 25 ^{\circ}\text{C}$	-	30	-	ns

Dual N-channel TrenchMOS logic level FET

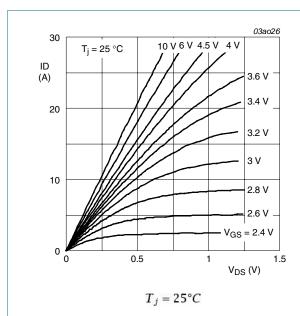


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical value

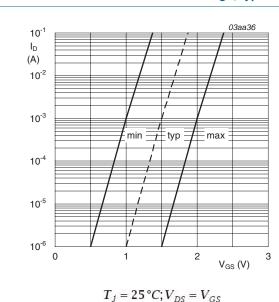
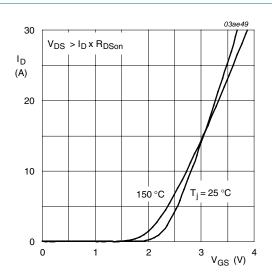
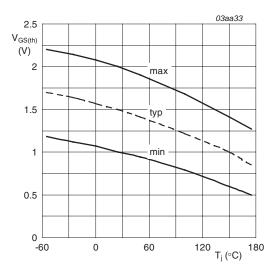


Fig 7. Sub-threshold drain current as a function of gate-source voltage



$$T_j = 25^{\circ}C$$
 and $150^{\circ}C$; $V_{DS} > I_D \times R_{DSon}$

Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values



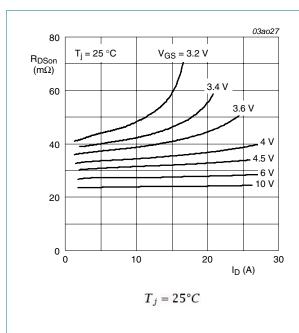
 $I_D = 1mA; V_{DS} = V_{GS}$

Fig 8. Gate-source threshold voltage as a function of junction temperature

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Drain-source on-state resistance as a function Fig 9. of drain current; typical values

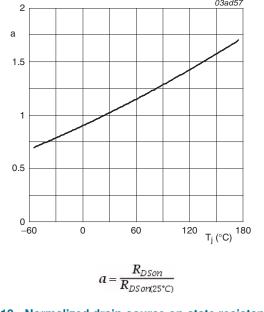


Fig 10. Normalized drain-source on-state resistance factor as a function of junction temperature

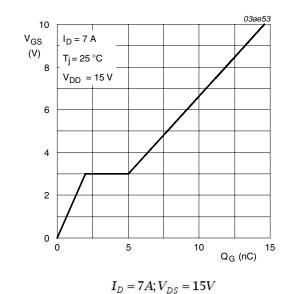
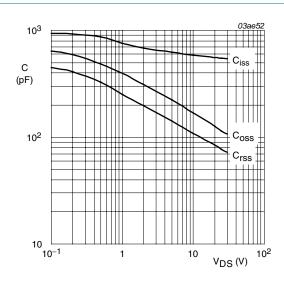


Fig 11. Gate-source voltage as a function of gate

charge; typical values



$$V_{GS} = 0V; f = 1MHz$$

Fig 12. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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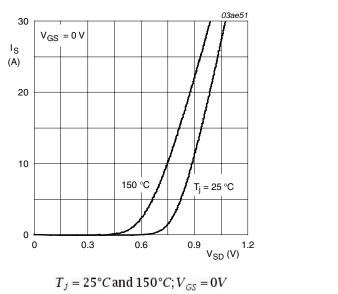


Fig 13. Source current as a function of source-drain voltage; typical values

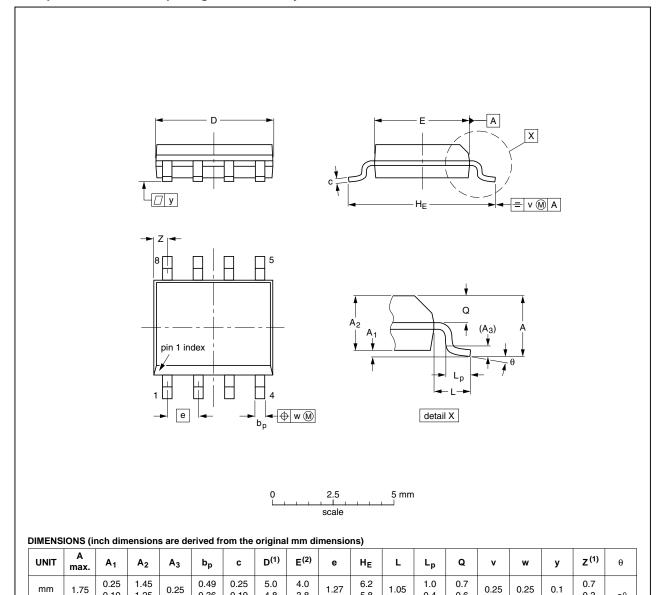
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Package outline

SO8: plastic small outline package; 8 leads; body width 3.9 mm

SOT96-1



inches

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

0.36

0.19

0.019 0.0100

0.014 0.0075

4.8

0.20

0.19

3.8

0.16

0.15

2. Plastic or metal protrusions of 0.25 mm (0.01 inch) maximum per side are not included.

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT96-1	076E03	MS-012			99-12-27 03-02-18

0.05

5.8

0.244

0.228

0.4

0.039

0.016

0.041

0.6

0.028

0.024

Fig 14. Package outline SOT96-1 (SO8)

1.25

0.057

0.049

0.01

0.10

0.010

0.004

0.069

0.3

0.028

0.004

0.01

0.01

00

Dual N-channel TrenchMOS logic level FET

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PHN203 _5	20100427	Product data sheet	-	PHN203 _4
Modifications:	 Various cha 	anges to content.		
PHN203 _4	20091208	Product data sheet	-	PHN203-03
PHN203 -03	20040126	Product data	-	PHN203 _2
PHN203_2	19990101	Product specification	-	PHN203 _1
PHN203 _1	19980204	Objective specification	-	-

Dual N-channel TrenchMOS logic level FET

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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Dual N-channel TrenchMOS logic level FET

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Dual N-channel TrenchMOS logic level FET

11. Contents

1	Product profile
1.1	General description1
1.2	Features and benefits1
1.3	Applications1
1.4	Quick reference data1
2	Pinning information
3	Ordering information2
4	Limiting values2
5	Thermal characteristics4
6	Characteristics5
7	Package outline
8	Revision history10
9	Legal information11
9.1	Data sheet status
9.2	Definitions11
9.3	Disclaimers
9.4	Trademarks12
10	Contact information